

THREE-DIMENSIONAL MEMORY AND FABRICATION METHOD THEREOF, MEMORY SYSTEM, AND ELECTRONIC APPARATUS

ABSTRACT

The present disclosure provides a three-dimensional memory and a fabrication method thereof, a memory system, and an electronic apparatus, and relates to the technical field of semiconductor chips. The three-dimensional memory includes a stack structure, an etch stop layer, a protective layer, and a plurality of connection pillars. The stack structure includes a gate layer and a dielectric layer disposed alternately and a plurality of steps. The etch stop layer is disposed on the steps. The protective layer covers the stack structure and the etch stop layer. The connection pillar penetrates through the protective layer and the etch stop layer on a corresponding step and is electrically connected with the gate layer of the corresponding step.

Fig. 5